优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

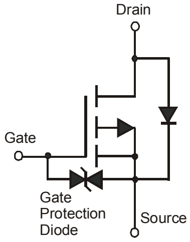
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

Mechanical Data

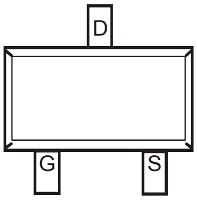
- Case: SOT-323
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 ⓔ3
- Weight: 0.006 grams (approximate)

ESD PROTECTED

Top View



Equivalent Circuit



Top View

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±6	V
Continuous Drain Current (Note 5)	Steady State	T_A = +25°C T_A = +85°C	I_D	-0.82 -0.54	A
Pulsed Drain Current (Note 6)			I_{DM}	-6	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.31	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	398	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	-	-	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	-100	nA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±2.0	μA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	-	-1.0	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	-	0.5	0.75	Ω	V_{GS} = -4.5V, I_D = -430mA
			0.7	1.05		V_{GS} = -2.5V, I_D = -300mA
			1.0	1.5		V_{GS} = -1.8V, I_D = -150mA
Forward Transfer Admittance	$\|Y_{fs}\|$	-	0.9	-	S	V_{DS} = -10V, I_D = -250mA
Diode Forward Voltage	V_{SD}		-0.8	-1.2	V	V_{GS} = 0V, I_S = -150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	59.76	-	pF	V_{DS} = -16V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	12.07	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	6.36	-	pF	
Total Gate Charge	Q_g	-	622.4	-	pC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -250mA
Gate-Source Charge	Q_{gs}	-	100.3	-	pC	
Gate-Drain Charge	Q_{gd}	-	132.2	-	pC	
Turn-On Delay Time	$t_{D(on)}$	-	5.1	-	ns	V_{DD} = -10V, V_{GS} = -4.5V, R_L = 47Ω, R_G = 10Ω, I_D = -200mA
Turn-On Rise Time	t_r	-	8.1	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	28.4	-	ns	
Turn-Off Fall Time	t_f	-	20.7	-	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

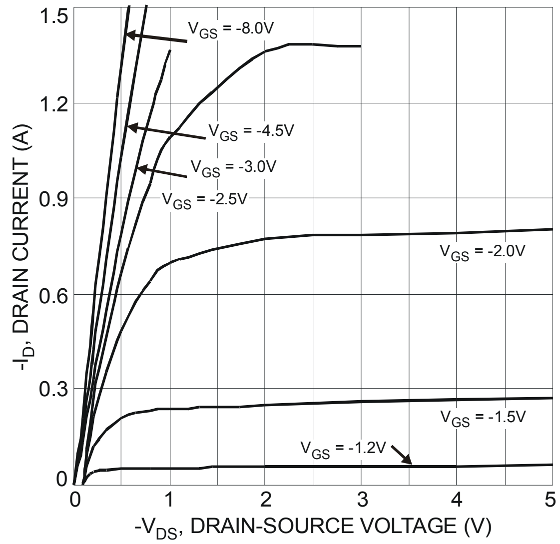


Fig. 1 Typical Output Characteristic

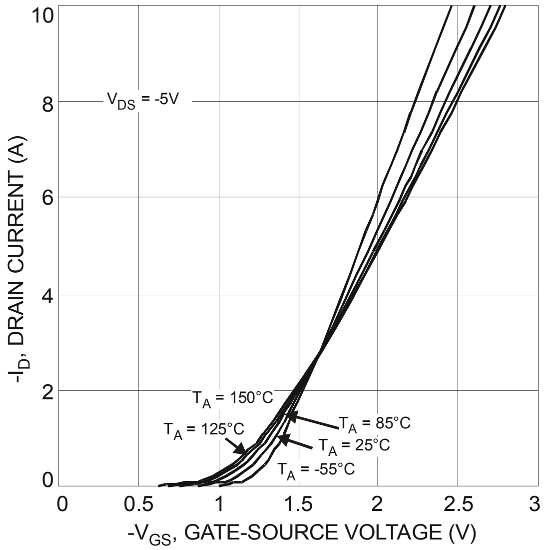


Fig. 2 Typical Transfer Characteristic

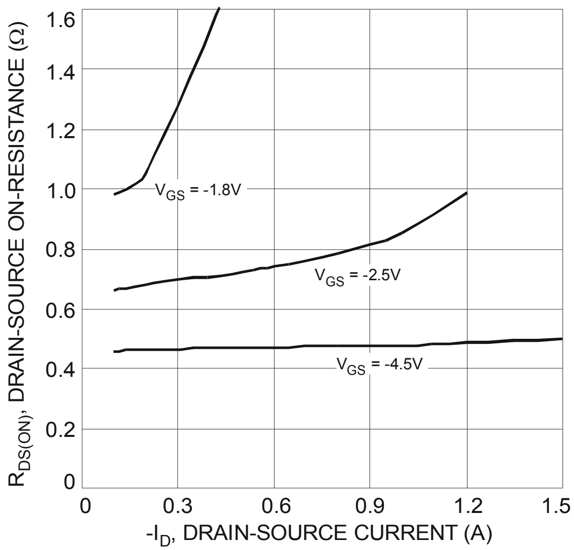


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

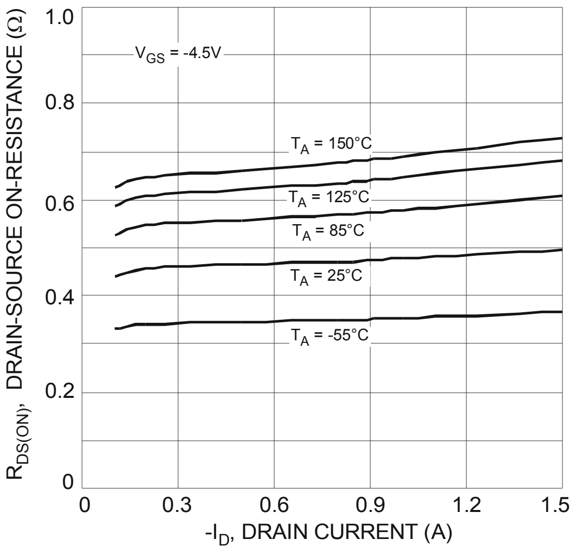


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

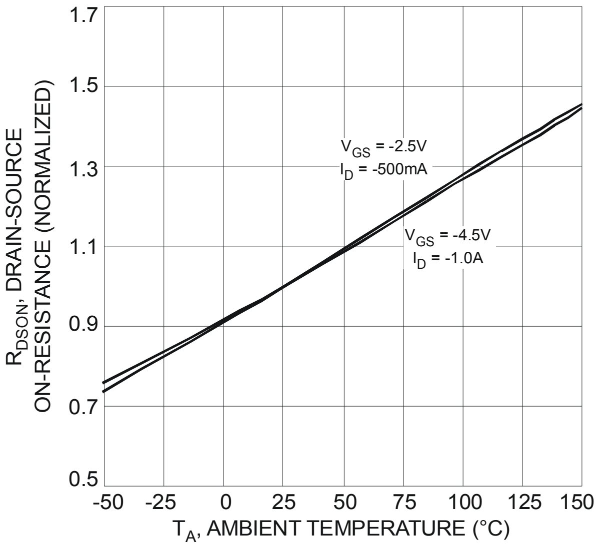


Fig. 5 On-Resistance Variation with Temperature

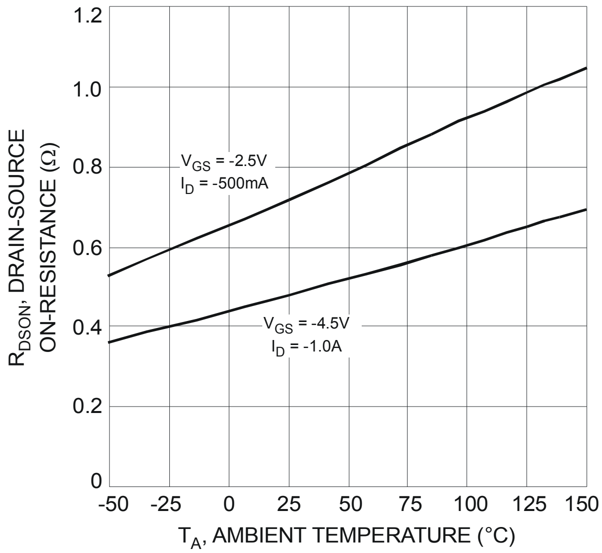


Fig. 6 On-Resistance Variation with Temperature

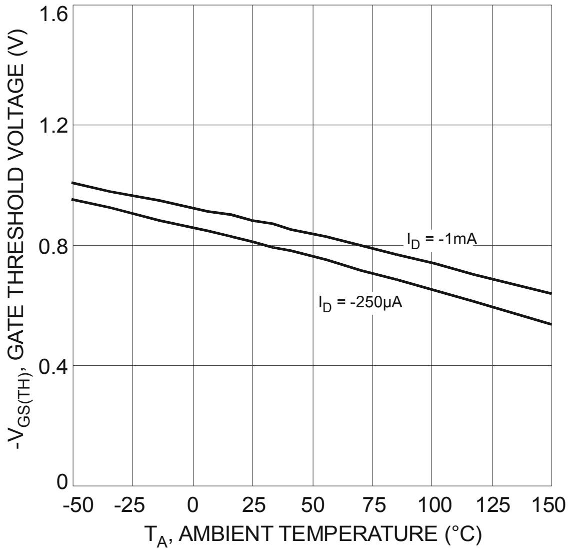


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

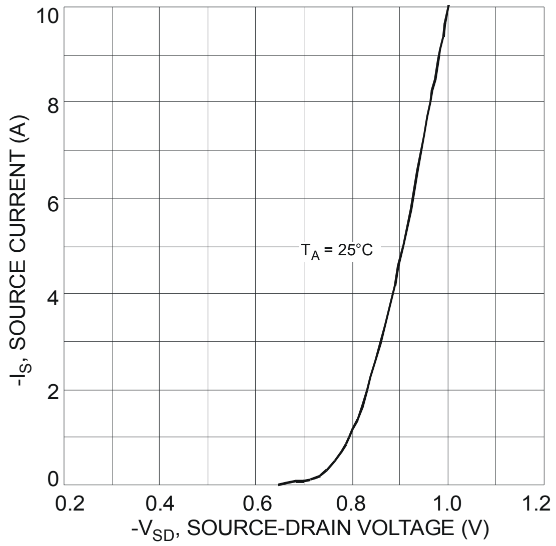


Fig. 8 Diode Forward Voltage vs. Current

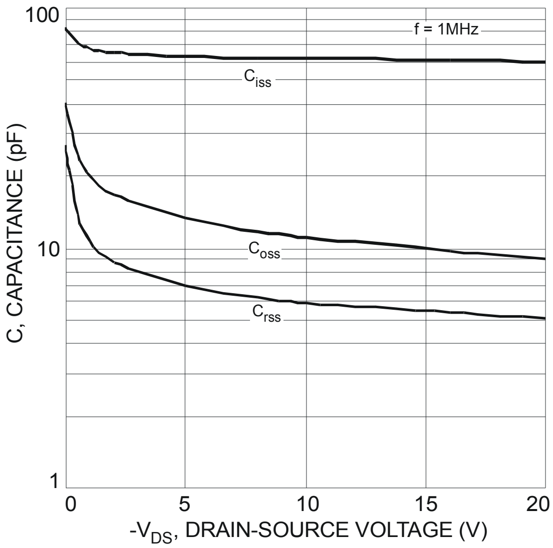


Fig. 9 Typical Total Capacitance

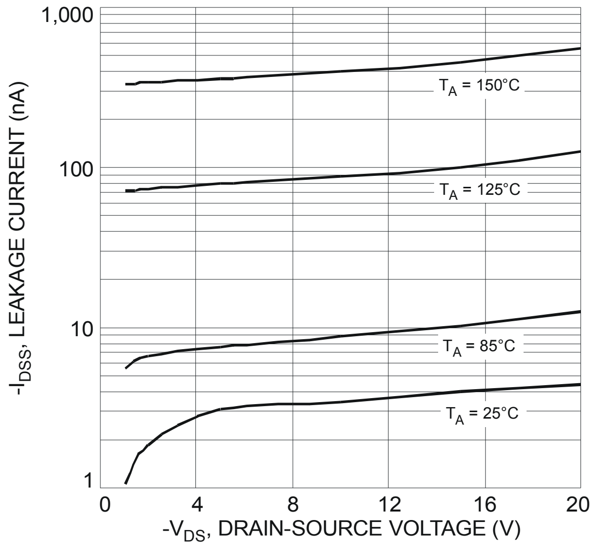


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

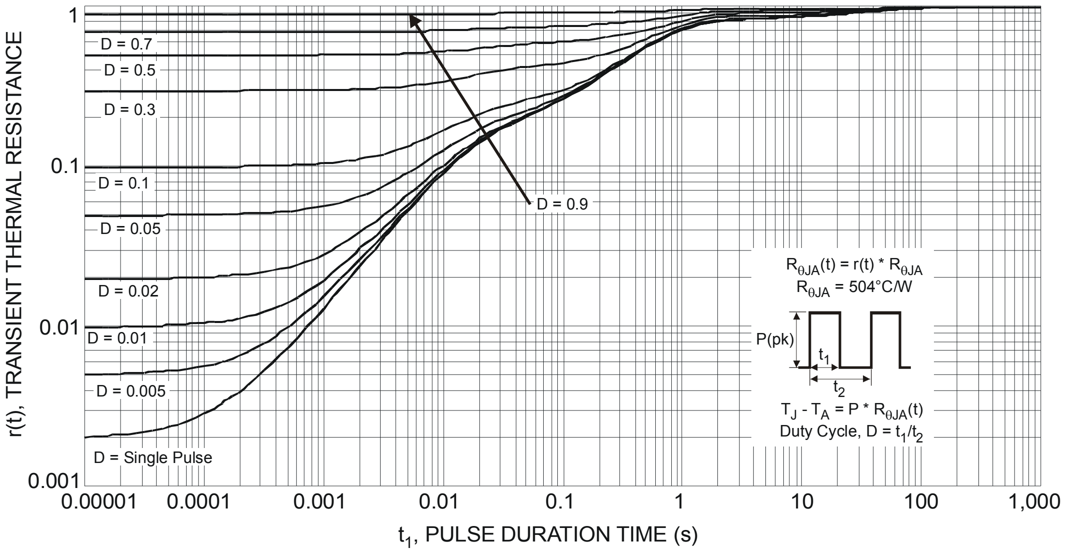
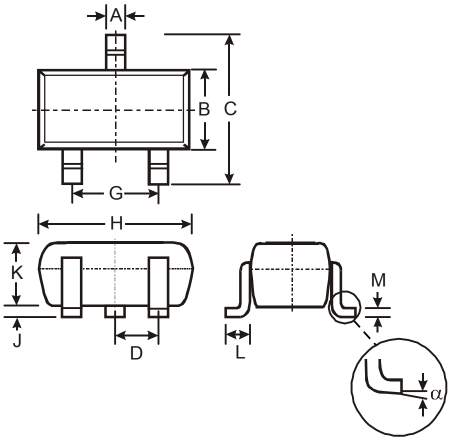


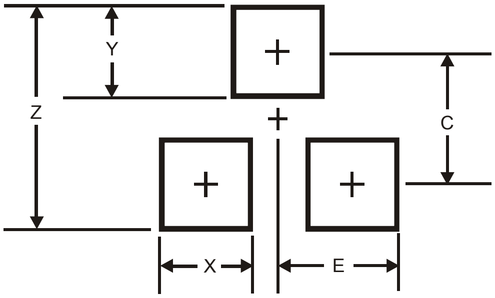
Fig. 11 Transient Thermal Response

Package Outline Dimensions



SOT-323			
Dim	**Min**	**Max**	**Typ**
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	0.95
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0